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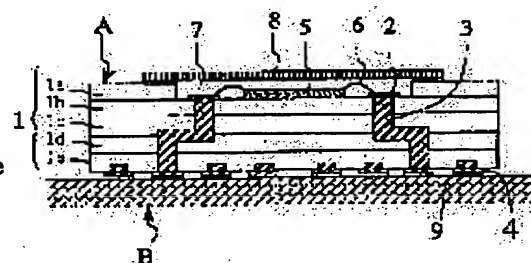
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**(54) GLASS COMPOSITION, GLASS SINTERED COMPACT AND WIRING BOARD OBTAINED BY USING THE SINTERED COMPACT**

(57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a wiring board which can be burned at  $\leq 1,000^{\circ}\text{C}$ , and in which a wiring layer containing low resistance metal can simultaneously be formed by burning, and which has a thermal expansion coefficient suitable for the packaging of GaAs chips, and a low Young's modulus, and ensures the long term reliability of connecting parts.

**SOLUTION:** In the wiring board provided with a wiring layer 2 containing low resistance metal provided on the surface and/or the inside of an insulation board 1, as the insulation board 1, a glass sintered compact is used which is obtained by molding glass powder containing, by weight, 10 to 40%  $\text{SiO}_2$ , 1 to 30%  $\text{Al}_2\text{O}_3$ , 10 to 40%  $\text{BaO}$ , 1 to 20%  $\text{Y}_2\text{O}_3$ , 0 to 30%  $\text{B}_2\text{O}_3$ , 0 to 25%  $\text{ZnO}$ , 0 to 20% of at least one kind selected from the group consisting of  $\text{MgO}$ ,  $\text{CaO}$  and  $\text{SrO}$ , and 0 to 10% of at least one kind selected from the group consisting of  $\text{ZrO}_2$ ,  $\text{SnO}_2$  and  $\text{TiO}_2$ , and  $\geq 90\%$  the total content of the above components, and thereafter performing burning thereto at  $\leq 1,000^{\circ}\text{C}$ .

**LEGAL STATUS**

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